

Amendments to the specification:

Please replace the paragraph which begins at page 5, line 24 and ends at page 6 line 2 with the amended paragraph blow:

-- ~~Diagrams~~ Figures 1-6 show the wafer profile of BSG wafers after the etching operation with two mixtures which are the subject-matter of the application and with spin etch F, a comparative solution. It is clearly evident from these that the layer thickness after etching with spin etch F is significantly less uniform than after etching with the mixtures in accordance with the present invention. All etching experiments were carried out with the same parameters. --